

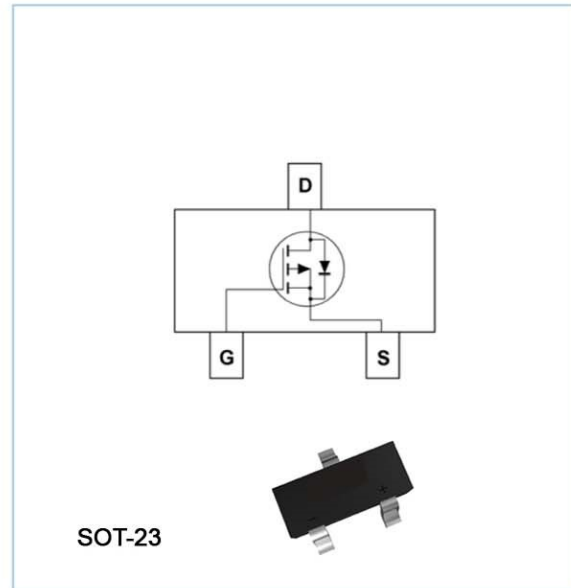
## P-Channel Enhancement Mode MOSFET

### Feature

- -16V/-3A,  $R_{DS(ON)} = 160\text{m}\Omega$  (MAX) @ $V_{GS} = -4.5\text{V}$ .  
 $R_{DS(ON)} = 240\text{m}\Omega$  (MAX) @ $V_{GS} = -2.5\text{V}$ .
- Super High dense cell design for extremely low  $R_{DS(ON)}$
- Reliable and Rugged
- SOT-23 for Surface Mount Package

### Applications

- Power Management  
Portable Equipment and Battery Powered Systems.



### Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$  Unless Otherwise noted

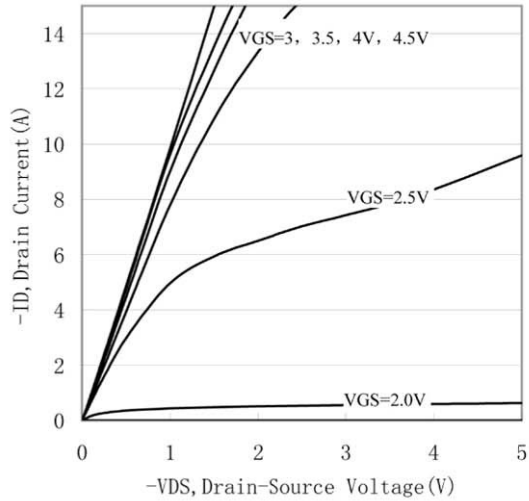
Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	-16	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Drain Current-Continuous	$I_D$	-3	A

### Electrical Characteristics

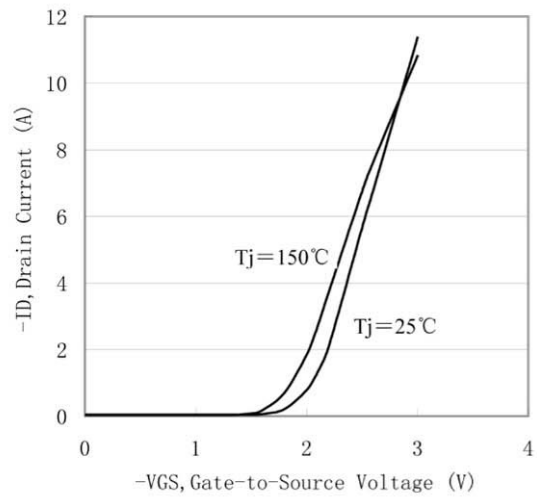
$T_A = 25^\circ\text{C}$  Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-16	-	-	V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -12\text{V}, V_{GS} = 0\text{V}$	-	-	-5	$\mu\text{A}$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 8\text{V}, V_{DS} = 0\text{V}$	-	-	100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -8\text{V}, V_{DS} = 0\text{V}$	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	-0.45	-	-1.5	V
Static Drain-source	$R_{DS(ON)}$	$V_{GS} = -4.5\text{V}, I_D = -3.0\text{A}$	-	-	160	$\text{m}\Omega$
On-Resistance		$V_{GS} = -2.5\text{V}, I_D = -2.0\text{A}$	-	-	240	$\text{m}\Omega$
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	VSD	$V_{GS} = 0\text{V}, I_S = -1.25\text{A}$			-1.8	V

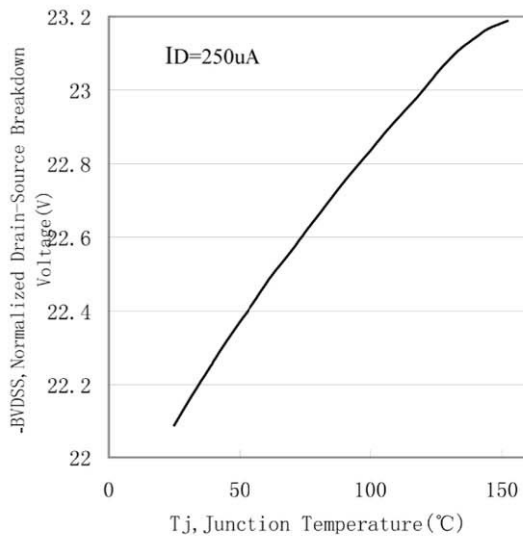
## Typical Characteristics



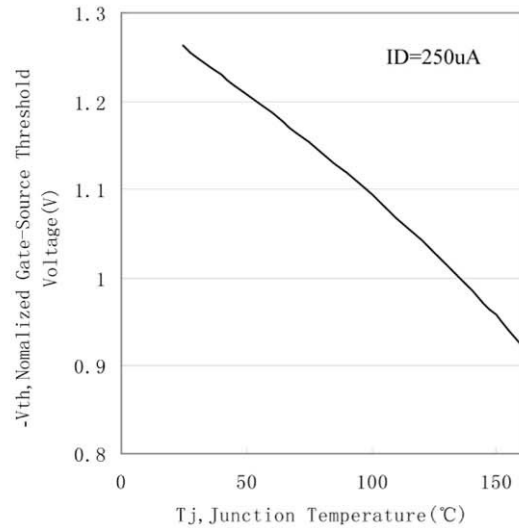
**Figure 1. Output Characteristics**



**Figure 2. Transfer Characteristics**



**Figure 3. Breakdown Voltage Variation with Temperature**



**Figure 4. Gate Threshold Variation with Temperature**